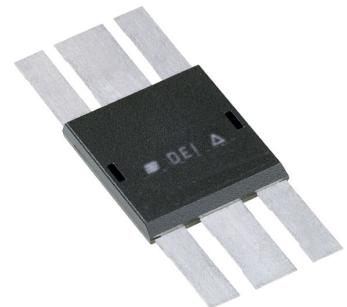




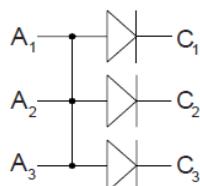
SS150TA60110, SS150TC60110, SS150TI60110

Silicon Carbide Schottky Diode

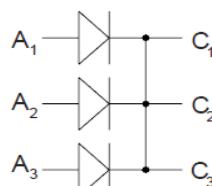
Part Number	V_{RRM} (V)	$I_{F(AVG)}$ (A)	Configuration
SS150TA60110	600	10	Triple Common Anode
SS150TC60110	600	10	Triple Common Cathode
SS150TI60110	600	10	Triple Independent

 $V_{RRM} = 600 \text{ V}$ $I_{F(AVG)} = 10 \text{ A}$ $C_J = 80 \text{ pF}$ 

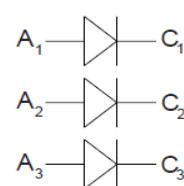
Triple Anode (TA)



Triple Cathode (TC)



Triple Independent (TI)



A = Anode C = Cathode

Symbol	Parameter	Test Conditions	Maximum Ratings	
V_{RRM}	Repetitive Peak Reverse Voltage		600	V
V_{RSM}	Repetitive Surge Reverse Voltage		600	V
V_{DC}	DC Blocking Voltage		600	V
$I_{F(AVG)}$	Average Forward Current	$T_J = 175^\circ\text{C}$	10	A
I_{FRM}	Repetitive Peak Forward Surge Current	$T_{VJ} = 45^\circ\text{C}$, $t_p = 10 \text{ ms}$ Half Sine Wave D = 0.3	25	A
T_{VJ}	Operating Virtual Junction Temperature		-55 to +175	$^\circ\text{C}$
T_{STG}	Storage Temperature		-55 to +175	$^\circ\text{C}$
P_{TOT}	$T_C = 25^\circ\text{C}$ (20 W/device)		60	W

Features

- 600 V SiC Schottky Diode
- Surface Mount Package
- Zero Reverse Recovery
- Zero Forward Recovery
- High Frequency Operation
- Temperature Independent Behavior
- Positive Temperature Coefficient for V_F

Applications

- MHz Switch Mode Power Supplies
- High Frequency Converters
- Resonant Converters
- Rectifier Circuits

Symbol	Parameter	Test Conditions	Characteristic Values		
			Typ.	Max.	Units
	$T_J = 25^\circ\text{C}$ unless otherwise specified				
V_F	Forward Voltage	$I_F = 5 \text{ A}$, $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	1.6 2	1.8 2.4	V
I_R	Reverse Current	$V_R = 600 \text{ V}$, $T_J = 25^\circ\text{C}$ $T_J = 175^\circ\text{C}$	10 20	50 200	μA
C_J	Junction Capacitance	$f = 1 \text{ MHz}$, $V_R = 0 \text{ V}$ $V_R = 200 \text{ V}$ $V_R = 600 \text{ V}$	485 85 80		pF
R_{THJC}	Thermal Resistance		2.5		$^\circ\text{C/W}$
T_L	Lead Soldering Temperature	1.6 mm (0.063 in) from case for 10 s	300		$^\circ\text{C}$
Isolation	Pin to Substrate Pin to Pin		>1800 >1500		VRMS
Weight			2		g

Fig. 1

Forward Voltage vs. Current

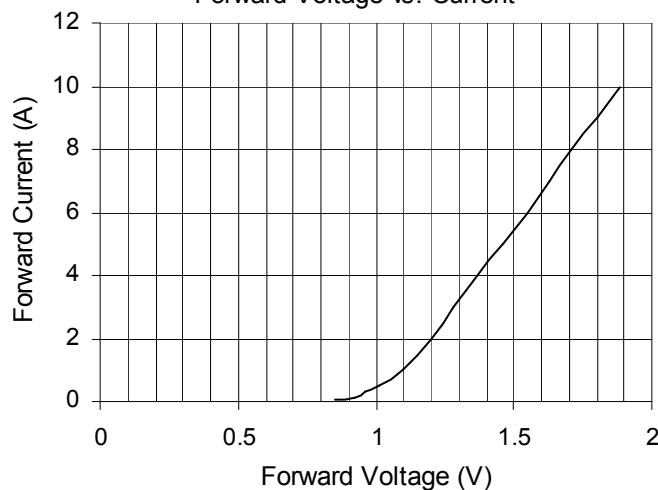


Fig. 2

Capacitance vs. Reverse Voltage

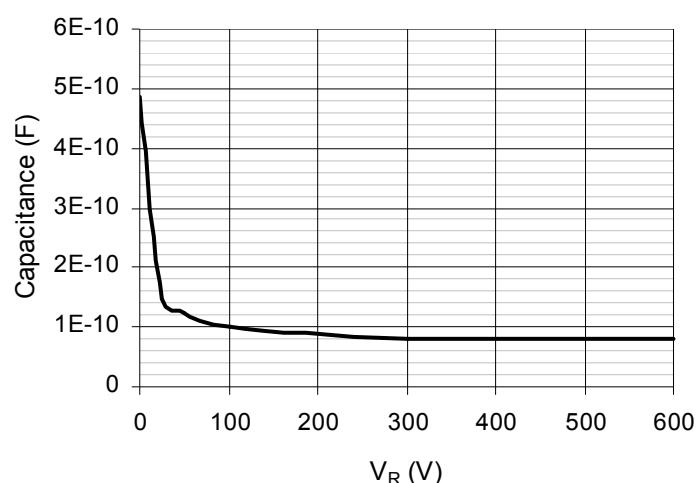


Fig. 3

Leakage Current vs. Reverse Voltage

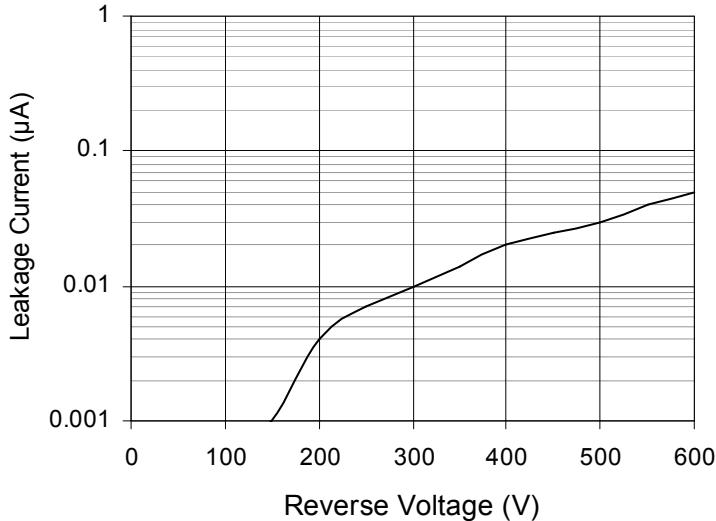


Fig. 4

Forward Voltage vs. Temperature

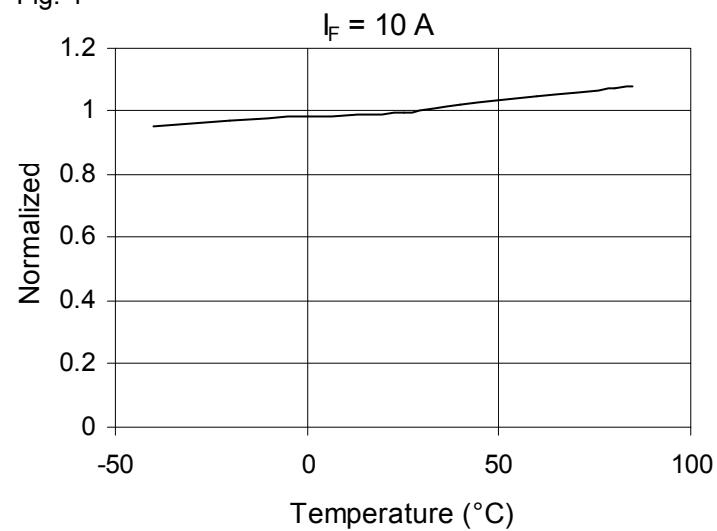


Fig. 5

Leakage Current vs. Temperature

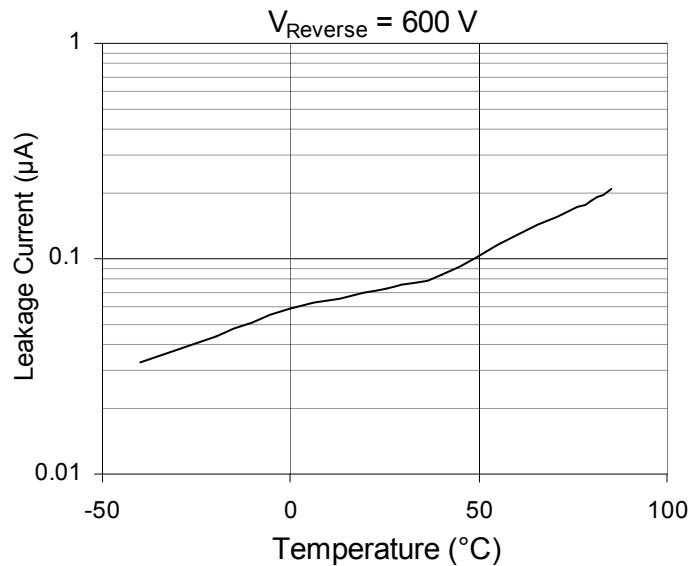
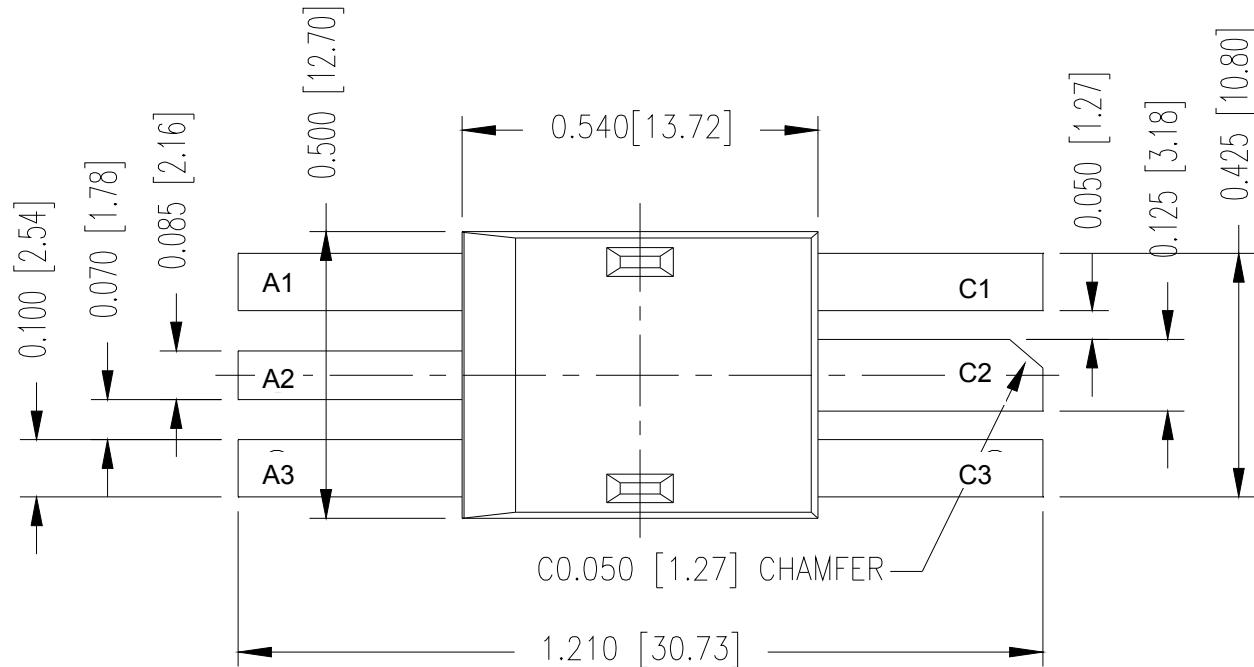
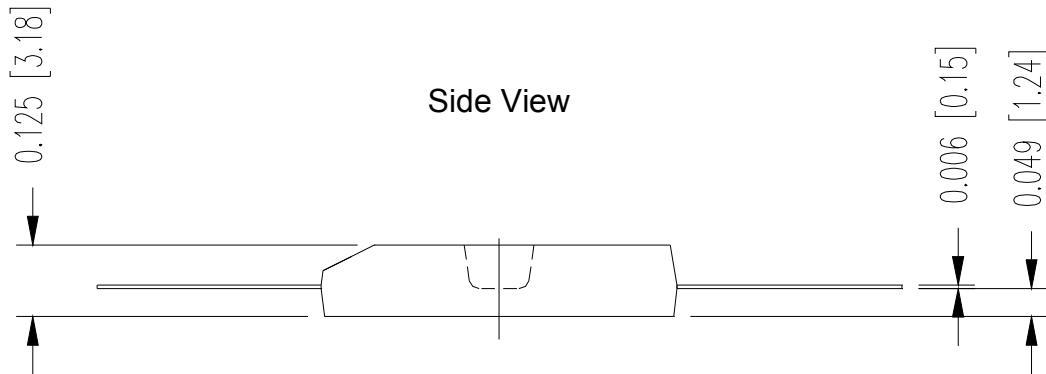


Fig. 6 Package Diagram

Top View



Side View



© 2013 IXYS RF

An IXYS Company

1609 Oakridge Dr., Suite 100

Fort Collins, CO USA 80525

970-493-1901 Fax: 970-232-3025

Email: sales@ixyscolorado.com

Web: <http://www.ixyscolorado.com>

DCB – Direct Copper Bond under Nickel plate on an Aluminum Nitride substrate, electrically isolated from any pin.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Schottky Diodes & Rectifiers category:

Click to view products by IXYS manufacturer:

Other Similar products are found below :

[CUS06\(TE85L,Q,M\)](#) [MA4E2039](#) [D1FH3-5063](#) [MBR0530L-TP](#) [MBR10100CT-BP](#) [MBR30H100MFST1G](#) [MMBD301M3T5G](#) [PMAD1103-LF](#) [PMAD1108-LF](#) [RB160M-50TR](#) [RB520S-30](#) [RB551V-30](#) [DD350N18K](#) [DZ435N40K](#) [DZ600N16K](#) [BAS16E6433HTMA1](#) [BAS 3010S-02LRH E6327](#) [BAT 54-02LRH E6327](#) [IDL02G65C5XUMA1](#) [NSR05F40QNXT5G](#) [JANS1N6640](#) [SB07-03C-TB-H](#) [SB1003M3-TL-W](#) [SBAT54CWT1G](#) [SK32A-LTP](#) [SK33A-TP](#) [SK34A-TP](#) [SK34B-TP](#) [SMD1200PL-TP](#) [ACDBN160-HF](#) [SS3003CH-TL-E](#) [STPS30S45CW](#) [PDS3100Q-7](#) [GA01SHT18](#) [CRS10I30A\(TE85L,QM\)](#) [MA4E2501L-1290](#) [MBR1240MFST1G](#) [MBRB30H30CT-1G](#) [BAS28E6433HTMA1](#) [BAS 70-02L E6327](#) [HSB123JTR-E](#) [JANTX1N5712-1](#) [VS-STPS40L45CW-N3](#) [DD350N12K](#) [SB007-03C-TB-E](#) [SK110-LTP](#) [SK154-TP](#) [SK32A-TP](#) [SK33B-TP](#) [SK35A-TP](#)